

## ABSTRACT OF THE DISCLOSURE

A nitride compound semiconductor light emitting device includes: a GaN substrate having a crystal orientation which is tilted away from a  $\langle 0001 \rangle$  direction by an angle which is equal to or greater than about  $0.05^\circ$  and which is equal to or less than about  $2^\circ$ , and a semiconductor multilayer structure formed on the GaN substrate, wherein the semiconductor multilayer structure includes: an acceptor doping layer containing a nitride compound semiconductor; and an active layer including a light emitting region.

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